

## SMALL SIGNAL SCHOTTKY DIODE

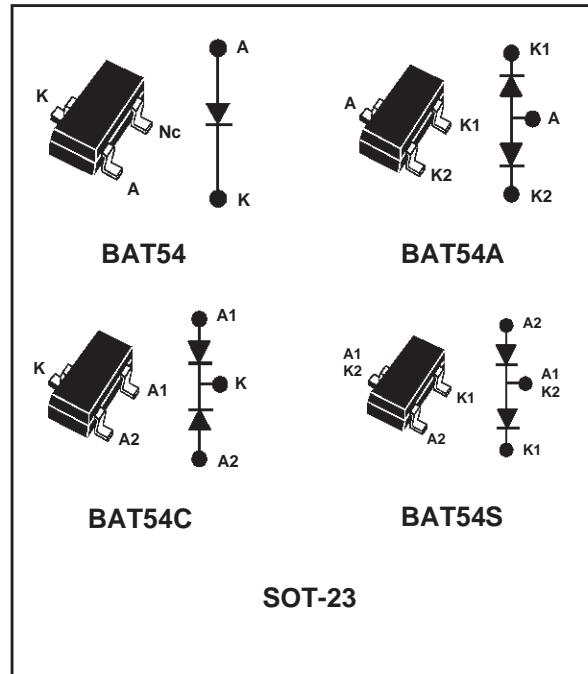
### FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- SURFACE MOUNT DEVICE

### DESCRIPTION

Schottky barrier diodes encapsulated in a SOT-23 small SMD packages.

Double diodes with different pinning are available.



### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	30	V
$I_F$	Continuous forward current	0.3	A
$I_{FSM}$	Surge non repetitive forward current tp=10ms sinusoidal	1	A
$P_{tot}$	Power dissipation (note 1) $T_{amb} = 25^\circ\text{C}$	250	mW
$T_{stg}$	Maximum storage temperature range	- 65 to +150	$^\circ\text{C}$
$T_j$	Maximum operating junction temperature *	150	$^\circ\text{C}$
$T_L$	Maximum temperature for soldering during 10s	260	$^\circ\text{C}$

Note 1: for double diodes,  $P_{tot}$  is the total dissipation of both diodes.

$$* : \frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)} \text{ thermal runaway condition for a diode on its own heatsink}$$

## BAT54, A, C, S

### THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient (*)	500	°C/W

(\*) Mounted on epoxy board with recommended pad layout.

### STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameters	Tests conditions		Min.	Typ.	Max.	Unit
$V_F^*$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 0.1 \text{ mA}$			240	mV
			$I_F = 1 \text{ mA}$			320	
			$I_F = 10 \text{ mA}$			400	
			$I_F = 30 \text{ mA}$			500	
			$I_F = 100 \text{ mA}$			900	
$I_R^{**}$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = 30 \text{ V}$			1	$\mu\text{A}$
		$T_j = 100^\circ\text{C}$				100	

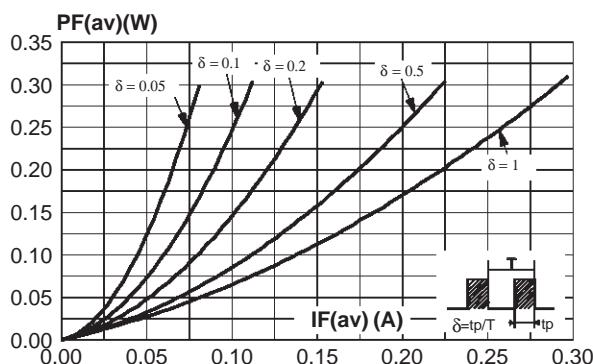
Pulse test : \*  $t_p = 380 \mu\text{s}, \delta < 2\%$

\*\*  $t_p = 5 \text{ ms}, \delta < 2\%$

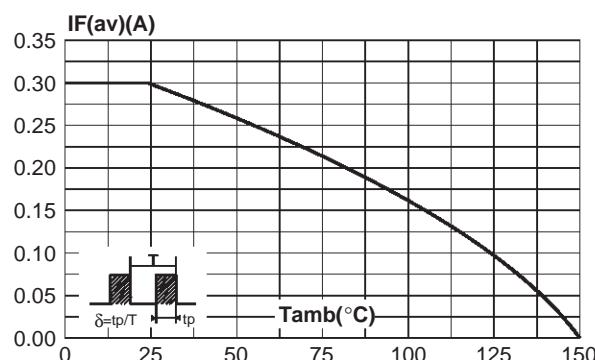
### DYNAMIC CHARACTERISTICS ( $T_j = 25^\circ\text{C}$ )

Symbol	Parameters	Tests conditions		Min.	Typ.	Max.	Unit
C	Junction capacitance	$T_j = 25^\circ\text{C} \quad V_R = 1 \text{ V} \quad F = 1 \text{ MHz}$				10	pF
$t_{rr}$	Reverse recovery time	$I_F = 10 \text{ mA} \quad I_R = 10 \text{ mA} \quad T_j = 25^\circ\text{C}$				5	ns
		$I_{rr} = 1 \text{ mA} \quad R_L = 100 \Omega$					

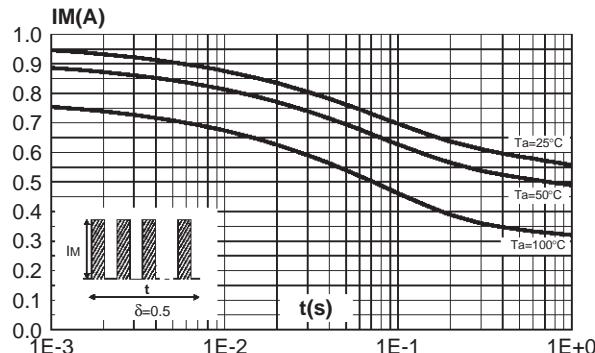
**Fig.1 :** Average forward power dissipation versus average forward current.



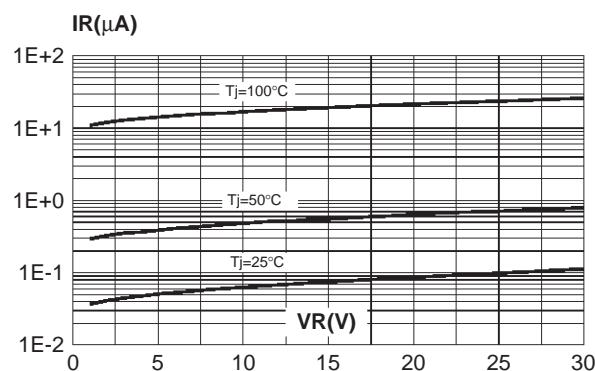
**Fig.2 :** Average forward current versus ambient temperature ( $\delta = 1$ ).



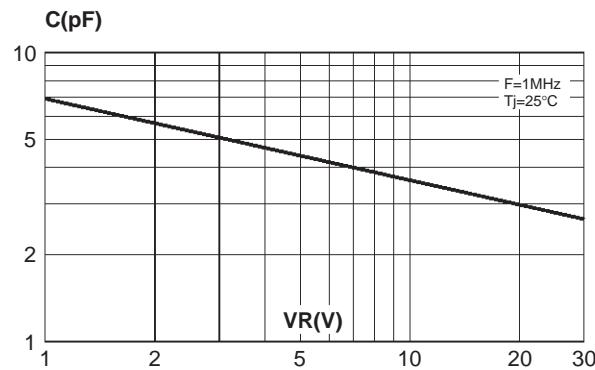
**Fig.3 :** Non repetitive surge peak forward current versus overload duration (maximum values).



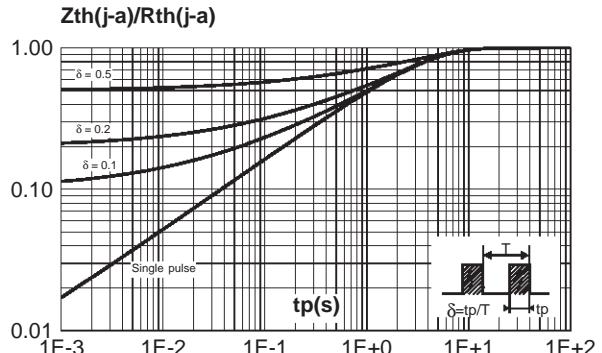
**Fig.5 :** Reverse leakage current versus reverse voltage applied (typical values).



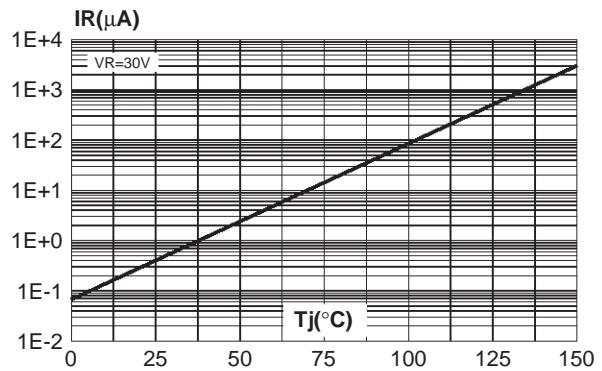
**Fig.7 :** Junction capacitance versus reverse voltage applied (typical values).



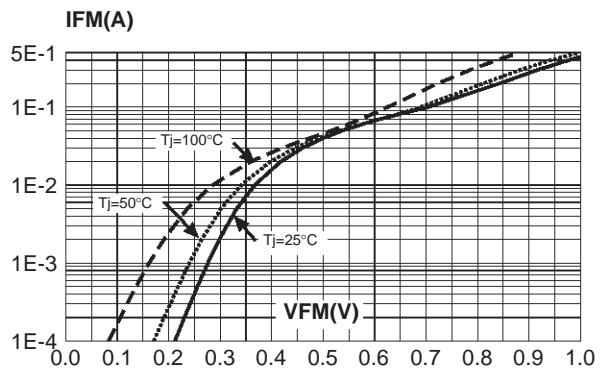
**Fig.4 :** Relative variation of thermal impedance junction to ambient versus pulse duration (alumine substrate 10mm x 8mm x 0.5mm).



**Fig.6 :** Reverse leakage current versus junction temperature.

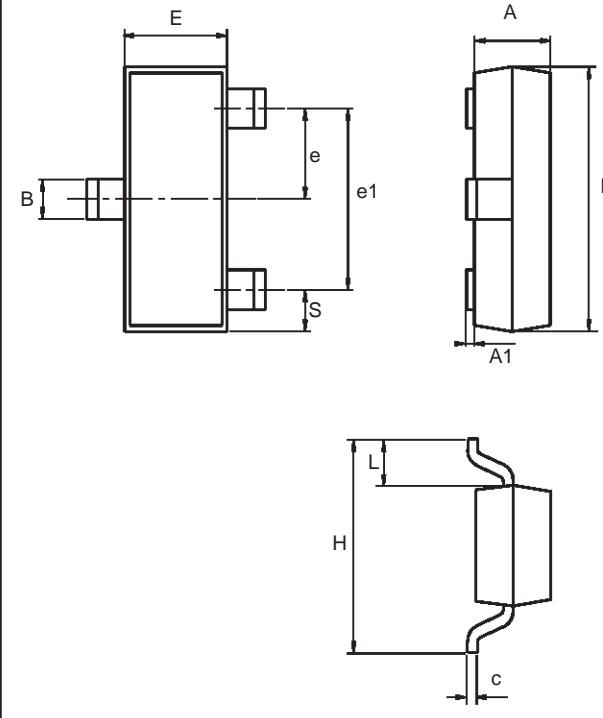


**Fig.8 :** Forward voltage drop versus forward current (typical values).



## BAT54, A, C, S

### PACKAGE MECHANICAL DATA SOT-23



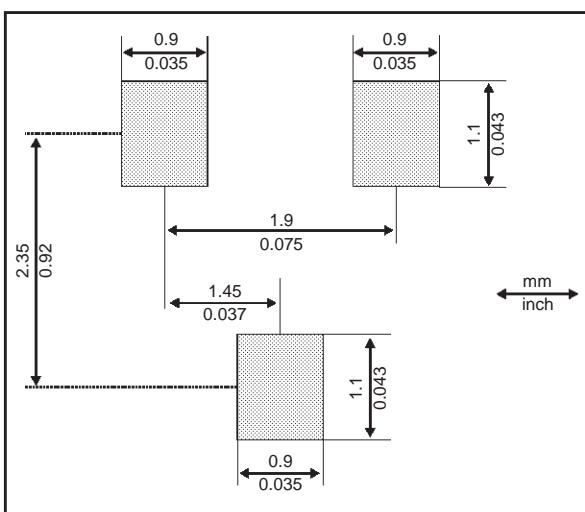
REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.89	1.4	0.035	0.055
A1	0	0.1	0	0.004
B	0.3	0.51	0.012	0.02
c	0.085	0.18	0.003	0.007
D	2.75	3.04	0.108	0.12
e	0.85	1.05	0.033	0.041
e1	1.7	2.1	0.067	0.083
E	1.2	1.6	0.047	0.063
H	2.1	2.75	0.083	0.108
L	0.6 typ.		0.024 typ.	
S	0.35	0.65	0.014	0.026

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BAT54FILM	D86	SOT-23	0.01g	3000	Tape & reel
BAT54AFILM	D84	SOT-23	0.01g	3000	Tape & reel
BAT54CFILM	D87	SOT-23	0.01g	3000	Tape & reel
BAT54SFILM	D88	SOT-23	0.01g	3000	Tape & reel

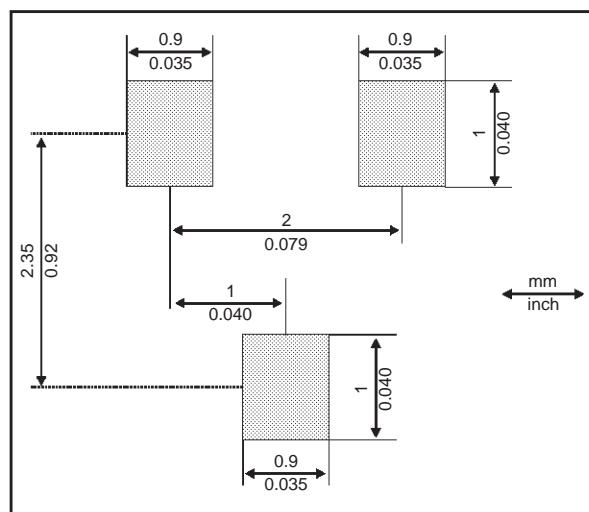
■ Epoxy meets UL94,V0

**FOOTPRINT DIMENSIONS**

COMPATIBLE SOT-23 / SC-59  
(in millimeters and inches)

**OPTIMIZED SOT-23 FOOTPRINT DIMENSIONS**

(in millimeters and inches)



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